

Sub C17
Q1 device, wherein, a material having a tensile stress of 8×10^9 dynes/cm² or more is formed in contact with a semiconductor film that is formed on a substrate, whereby an impurity element in said semiconductor film is gettered into said material.

Q2 7. (Amended) A method of manufacturing a semiconductor device, wherein a material formed by LPCVD within a temperature range of between 500 and 900°C is formed in contact with a semiconductor film that is formed on a substrate, whereby an impurity element in said semiconductor film is gettered into said material. C

8. (Amended) A method of manufacturing a semiconductor device, wherein a material formed by LPCVD within a pressure range of between 0.1 and 3 Torr is formed in contact with a semiconductor film that is formed on a substrate, whereby an impurity element in said semiconductor film is gettered into said material.

9. (Amended) A method of manufacturing a semiconductor device, wherein a material formed by LPCVD with a gas containing chlorine as a material gas is formed in contact with a semiconductor film that is formed on a substrate, whereby an impurity element in said semiconductor film is gettered into

said material.

Sub C.7
10. (Amended) A method of manufacturing a semiconductor device, wherein a silicon nitride film having an N/Si composition ratio of between 1.2 and 1.4 is formed in contact with a semiconductor film that is formed on a substrate, whereby an impurity element in said semiconductor film is gettered into said silicon nitride film.

Q2
11. (Amended) A method of manufacturing a semiconductor device, wherein a silicon nitride film formed by LPCVD is formed in contact with a semiconductor film that is formed on a substrate, whereby an impurity element in said semiconductor film is gettered into said silicon nitride film.

Q3
18. (Amended) A method of manufacturing a semiconductor device according to any one of claims 1 and 7 to 11, wherein said semiconductor film is a non-single crystal semiconductor film.

19. (Amended) A method of manufacturing a semiconductor device according to any one of claims 1 and 7 to 11, wherein said semiconductor film is a crystalline silicon film.

Sub C.7
Q4
21. (Amended) A method of manufacturing a semiconductor device, wherein after a material is formed in contact with a semiconductor film that is formed on a substrate, heat treatment is performed to thereby set a tensile stress of said material to 8×10^9 dynes/cm² or more and at the same time an impurity element in said semiconductor film is gettered into said material.

Q5
31. (Amended) A method of manufacturing a semiconductor device, wherein after a material is formed in contact with a semiconductor film that is formed on a substrate, heat treatment is performed to thereby set a composition ratio of N/Si of said material to between 1.2 and 1.4 and at the same time an impurity element in said semiconductor film is gettered into said material.

Please add the following new claims 44-59.

Q6
44. (New) A method of manufacturing a semiconductor device according to claim 1, wherein said semiconductor film is formed by crystallizing an amorphous semiconductor film which is intentionally introduced a metallic element for promoting crystallization by performing a heat treatment.

Sub C1 7
45. (New) A method of manufacturing a semiconductor device according to claim 7, wherein said semiconductor film is formed by crystallizing an amorphous semiconductor film which is intentionally introduced a metallic element for promoting crystallization by performing a heat treatment.

46. (New) A method of manufacturing a semiconductor device according to claim 8, wherein said semiconductor film is formed by crystallizing an amorphous semiconductor film which is intentionally introduced a metallic element for promoting crystallization by performing a heat treatment.

47. (New) A method of manufacturing a semiconductor device according to claim 9, wherein said semiconductor film is formed by crystallizing an amorphous semiconductor film which is intentionally introduced a metallic element for promoting crystallization by performing a heat treatment.

48. (New) A method of manufacturing a semiconductor device according to claim 10, wherein said semiconductor film is formed by crystallizing an amorphous semiconductor film which is intentionally introduced a metallic element for promoting crystallization by performing a heat treatment.

Sub 7
49. (New) A method of manufacturing a semiconductor device according to claim 11, wherein said semiconductor film is formed by crystallizing an amorphous semiconductor film which is intentionally introduced a metallic element for promoting crystallization by performing a heat treatment.

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50. (New) A method of manufacturing a semiconductor device according to claim 21, wherein said semiconductor film is formed by crystallizing an amorphous semiconductor film which is intentionally introduced a metallic element for promoting crystallization by performing a heat treatment.

51. (New) A method of manufacturing a semiconductor device according to claim 31, wherein said semiconductor film is formed by crystallizing an amorphous semiconductor film which is intentionally introduced a metallic element for promoting crystallization by performing a heat treatment.

52. (New) A method of manufacturing a semiconductor device according to claim 1, wherein said semiconductor film is formed by crystallizing an amorphous semiconductor film which is selectively introducing a metallic element for promoting crystallization by performing a heat treatment.

53. (New) A method of manufacturing a semiconductor device according to claim 7, wherein said semiconductor film is formed by crystallizing an amorphous semiconductor film which is selectively introducing a metallic element for promoting crystallization by performing a heat treatment.

54. (New) A method of manufacturing a semiconductor device according to claim 8, wherein said semiconductor film is formed by crystallizing an amorphous semiconductor film which is selectively introducing a metallic element for promoting crystallization by performing a heat treatment.

55. (New) A method of manufacturing a semiconductor device according to claim 9, wherein said semiconductor film is formed by crystallizing an amorphous semiconductor film which is selectively introducing a metallic element for promoting crystallization by performing a heat treatment.

56. (New) A method of manufacturing a semiconductor device according to claim 10, wherein said semiconductor film is formed by crystallizing an amorphous semiconductor film which is selectively introducing a metallic element for promoting crystallization by performing a heat treatment.

SUB 7
57. (New) A method of manufacturing a semiconductor device according to claim 11, wherein said semiconductor film is formed by crystallizing an amorphous semiconductor film which is selectively introducing a metallic element for promoting crystallization by performing a heat treatment.

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58. (New) A method of manufacturing a semiconductor device according to claim 21, wherein said semiconductor film is formed by crystallizing an amorphous semiconductor film which is selectively introducing a metallic element for promoting crystallization by performing a heat treatment.

59. (New) A method of manufacturing a semiconductor device according to claim 31, wherein said semiconductor film is formed by crystallizing an amorphous semiconductor film which is selectively introducing a metallic element for promoting crystallization by performing a heat treatment.
